

#### **General Description**

The MAX4843-MAX4846 overvoltage protection controllers protect low-voltage systems against high-voltage faults of up to 28V. When the input voltage exceeds the overvoltage threshold, these devices turn off a low-cost, external n-channel FET(s) to prevent damage to the protected components. An internal charge pump eliminates the need for external capacitors and drives the FET gate for a simple, robust solution.

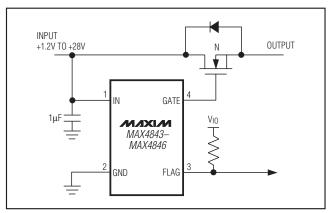
The overvoltage trip level is set to 7.4V (MAX4843), 6.35V (MAX4844), 5.8V (MAX4845), or 4.65V (MAX4846). When the input voltage drops below the undervoltage lockout (UVLO) threshold, the devices enter a low standby current mode (10µA). The MAX4843/MAX4844/MAX4845 have a UVLO threshold of 4.15V, the MAX4845C/MAX4845D have a UVLO threshold of 2.2V, and the MAX4846 has a UVLO threshold of 2.5V. In addition to the single FET configuration, the devices can be configured with back-toback external FETs to prevent currents from being back-driven into the adapter.

An additional feature includes a ±15kV ESD-protected input when bypassed with a 1µF capacitor to ground. All devices are offered in small 6-pin µDFN (1.5mm x 1.0mm) and 6-pin ultra-thin LGA (MAX4845 and MAX4846 only) (1.5mm x 1.0mm) packages and are specified for operation over the -40°C to +85°C temperature range.

## **Applications**

Cell Phones Digital Still Cameras PDAs and Palmtop Devices MP3 Players

## **Typical Operating Circuit**



## **Features**

- ♦ Overvoltage Protection Up to 28V
- ♦ Preset 7.4V, 6.35V, 5.8V, or 4.65V Overvoltage Trip
- ♦ Low (10µA) Undervoltage Lockout Standby Current
- **♦ Drives Low-Cost nMOSFET**
- ♦ Internal 50ms Startup Delay
- **♦ Internal Charge Pump**
- ♦ Overvoltage Fault FLAG Indicator
- ♦ 6-Pin (1.5mm x 1.0mm) µDFN Package

### **Ordering Information**

PART	PIN- PACKAGE	UVLO (V)	OVLO (V)	TOP MARK
MAX4843ELT	6 µDFN	4.15	7.40	BE
MAX4844ELT	6 μDFN	4.15	6.35	BF
MAX4845ELT	6 µDFN	4.15	5.80	BG
MAX4845EYT+T	6 UTLGA	4.15	5.80†	AC
MAX4845CEYT+T	6 UTLGA	2.20	5.80†	AP
MAX4845DEYT+T	6 UTLGA	2.20	5.80	AQ
MAX4846ELT	6 µDFN	2.50	4.65	ВН
MAX4846EYT+T	6 UTLGA	2.50	4.65	AD

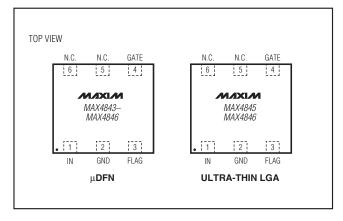
Note: All devices are specified over the -40°C to +85°C temperature range.

+Denotes a lead(Pb)-free/RoHS-compliant package.

T = Tape and reel.

†OVLO maximum is 6.0V for the MAX4845C and 5.9V for the MAX4845D.

## Pin Configurations



Maxim Integrated Products 1

#### **ABSOLUTE MAXIMUM RATINGS**

IN to GND0.3V to +30V GATE to GND0.3V to +12V	Operating Temperature Range40°C to +85°C Junction Temperature+150°C
FLAG to GND0.3V to +6V	Storage Temperature Range65°C to +150°C
Continuous Power Dissipation ( $T_A = +70^{\circ}C$ )	Soldering Temperature (reflow)
6-Pin µDFN (derate 2.1mW/°C above +70°C)167.7mW	6-Pin µDFN+240°C
6-Pin Ultra-Thin LGA (derate 2.1mW/°C	6-Pin Ultra-Thin LGA+260°C
above +70°C)170.2mW	

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### **ELECTRICAL CHARACTERISTICS**

 $(V_{IN} = +5V \text{ for MAX4843/MAX4844/MAX4845}, V_{IN} = +4V \text{ for MAX4846}, C_{GATE} = 500pF, T_A = -40^{\circ}C \text{ to } +85^{\circ}C, \text{ unless otherwise noted.}$  Typical values are at  $T_A = +25^{\circ}C$ .) (Note 1)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
Input Voltage Range	VIN			1.2		28.0	V
		V <sub>IN</sub> falling	MAX4843/MAX4844/MAX4845	3.9	4.15	4.4	V
Undervoltage Lockout Threshold	UVLO		MAX4845C/MAX4845D	1.8	2.2	2.5	
			MAX4846	2.3	2.5	2.7	
Undervoltage Lockout		MAX4843/N	1AX4844/MAX4845		41		mV
Hysteresis		MAX4846			25		IIIV
			MAX4843	7.0	7.4	7.8	
			MAX4844	6.0	6.35	6.7	
Overveltees Trip Level	OVLO	\/minima	MAX4845	5.5	5.8	6.1	- V
Overvoltage Trip Level	OVLO	V <sub>IN</sub> rising	MAX4845C	5.5	5.8	6.0	
			MAX4845D	5.5	5.8	5.9	
			MAX4846	4.35	4.65	4.95	
		MAX4843			75		
		MAX4844			65		mV
Overvoltage Lockout Hysteresis		MAX4845			55		TIIV
		MAX4846			50		
IN Supply Current	I <sub>IN</sub>	MAX4843/N	1AX4844/MAX4845		70	120	μΑ
in Supply Guilent	IIIN	MAX4846			60	110	μΑ
UVLO Supply Current	luvLo	$V_{IN} = 3.8V$	MAX4843/MAX4844/MAX4845		10	22	μΑ
Oveo Supply Current		$V_{IN} = 2.2V$	MAX4846		8	18	μΑ
Gate Voltage	VGATE	I 1uA load H	MAX4843/MAX4844/MAX4845	9	9.83	10	V
			MAX4846	7.5	7.85	8.0	V
GATE Pulldown Current	I <sub>PD</sub>	V <sub>IN</sub> > OVLO, V <sub>GATE</sub> = 5.5V		10	27		mA
FLAG Output Low Voltage	V <sub>OL</sub>	I <sub>SINK</sub> = 1mA, FLAG deasserted				0.4	V
FLAG Leakage Current		V <sub>FLAG</sub> = 5.5V, FLAG asserted				1	μΑ

#### **ELECTRICAL CHARACTERISTICS (continued)**

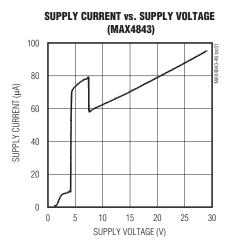
 $(V_{IN} = +5V \text{ for MAX4843/MAX4844/MAX4845}, V_{IN} = +4V \text{ for MAX4846}, C_{GATE} = 500pF, T_A = -40^{\circ}C \text{ to } +85^{\circ}C, \text{ unless otherwise noted. Typical values are at } T_A = +25^{\circ}C.)$  (Note 1)

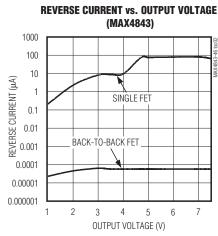
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
TIMING	•					
Startup Delay	tstart	V <sub>IN</sub> = UVLO rising to V <sub>GATE</sub> = 0.3V rising (Figure 1)	20	50	80	ms
FLAG Blanking Time	tBLANK	$V_{GATE} = 0.3V$ rising to $V_{FLAG} = 0.3V$ falling (Figure 1)	20	50	80	ms
Gate Turn-On Time	tGON	V <sub>GATE</sub> = 0.3V to 8V (MAX4843/MAX4844/MAX4845), V <sub>GATE</sub> = 0.3V to 7V (MAX4846) (Figure 1)		10		ms
Gate Turn-Off Time	tGOFF	V <sub>IN</sub> rising at 1V/µs from 5V to 8V (MAX4843/MAX4844/MAX4845) or from 4V to 7V (MAX4846) to V <sub>GATE</sub> = 0.3V (Figure 2)		6	20	μs
FLAG Assertion Delay	tFLAG	V <sub>IN</sub> rising at 1V/µs from 5V to 8V (MAX4843/MAX4844/MAX4845) or from 4V to 7V (MAX4846), to V <sub>FLAG</sub> = 2.4V, R <sub>FLAG</sub> = 10k to 3V (Figure 2)		5.8		μs
Initial Overvoltage Fault Delay	tovp	V <sub>IN</sub> rising at 1V/µs from 0V to 9V, time from V <sub>IN</sub> = 5V to I <sub>GATE</sub> = 80% of I <sub>PD</sub> (Figure 3)		1.5		μs

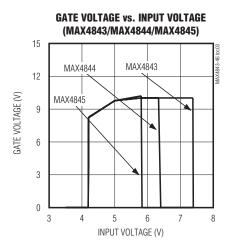
Note 1: All devices are 100% tested at +25°C. Electrical limits across the full temperature range are guaranteed by design and correlation.

## **Typical Operating Characteristics**

 $(V_{IN} = +5V \text{ for MAX4843/MAX4844/MAX4845}, V_{IN} = +4V \text{ for MAX4846}, T_A = +25^{\circ}C, \text{ unless otherwise noted.})$ 

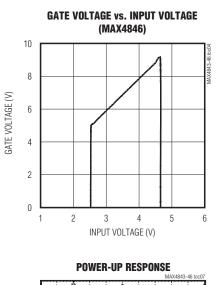


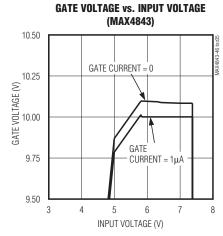


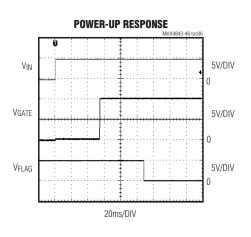


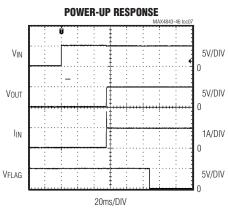
## Typical Operating Characteristics (continued)

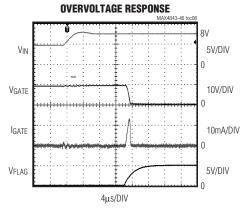
 $(V_{IN} = +5V \text{ for MAX4843/MAX4844/MAX4845}, V_{IN} = +4V \text{ for MAX4846}, T_A = +25^{\circ}C, \text{ unless otherwise noted.})$ 

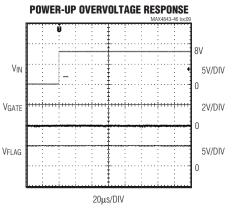








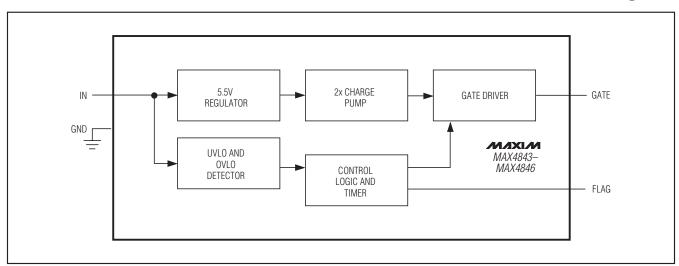




## **Pin Description**

Р	IN		FUNCTION	
μDFN	ULTRA- THIN LGA	NAME		
1	1	IN	Voltage Input. IN is both the power-supply input and the overvoltage sense input. Bypass IN to GND with a 1µF capacitor or larger.	
2	2	GND	Ground	
3	3	FLAG	Fault Indication Output. FLAG is asserted high during undervoltage lockout and overvoltage lockout conditions. FLAG is deasserted during normal operation. FLAG is an open-drain output.	
4	4	GATE	Gate-Drive Output. GATE is the output of an on-chip charge pump. When V <sub>UVLO</sub> < V <sub>IN</sub> < V <sub>OVLO</sub> , GATE is driven high to turn on the external n-channel MOSFET(s).	
5, 6	5, 6	N.C.	No Connection. Not internally connected. Do not connect.	

# Functional Diagram



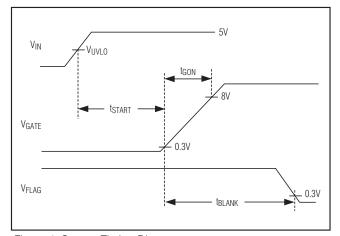


Figure 1. Startup Timing Diagram

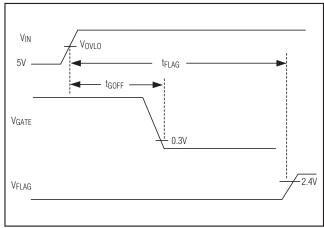


Figure 2. Shutdown Timing Diagram

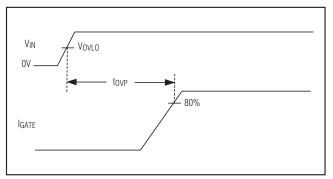


Figure 3. Power-Up Overvoltage Timing Diagram

### **Detailed Description**

The MAX4843–MAX4846 provide up to 28V overvoltage protection for low-voltage systems. When the input voltage exceeds the overvoltage trip level, the MAX4843–MAX4846 turn off a low-cost external n-channel FET(s) to prevent damage to the protected components. An internal charge pump (see the *Functional Diagram*) drives the FET gate for a simple, robust solution. On power-up, the device waits for 50ms before driving GATE high. The open-drain FLAG output is kept at high impedance for an additional 50ms after GATE goes high before deasserting. The FLAG output asserts high immediately to an overvoltage fault.

#### **Undervoltage Lockout (UVLO)**

The MAX4843/MAX4844/MAX4845 have a fixed 4.15V typical UVLO level, the MAX4845C/MAX4845D have a 2.2V typical UVLO, and the MAX4846 has a 2.5V typical UVLO. When  $V_{\rm IN}$  is less than the UVLO, the GATE driver is held low and FLAG is asserted.

#### Overvoltage Lockout (OVLO)

The MAX4843 has a 7.4V typical OVLO; the MAX4844 has a 6.35V typical OVLO; and the MAX4845 has a 5.8V typical OVLO. The MAX4846 has a 4.65V typical overvoltage threshold. When V<sub>IN</sub> is greater than OVLO, the GATE driver is held low and FLAG is asserted.

#### **FLAG Output**

The open-drain FLAG output is used to signal to the host system that there is a fault with the input voltage. FLAG asserts immediately to an overvoltage fault. FLAG is held high for 50ms after GATE turns on before deasserting. Connect a pullup resistor from FLAG to the logic I/O voltage of the host system.

#### **GATE Driver**

An on-chip charge pump is used to drive GATE above IN, allowing the use of low-cost n-channel MOSFETs. The charge pump operates from the internal 5.5V regulator.

The actual GATE output voltage tracks approximately two times V<sub>IN</sub> until V<sub>IN</sub> exceeds 5.5V or the OVLO trip level is exceeded, whichever comes first. The MAX4843 has a 7.4V typical OVLO, therefore GATE remains relatively constant at about 10.5V for 5.5V < V<sub>IN</sub> < 7.4V. The MAX4845 has a 5.8V typical OVLO, but this can be as low as 5.5V. The GATE output voltage as a function of input voltage is shown in the *Typical Operating Characteristics*.

#### **Device Operation**

The MAX4843–MAX4846 have an on-board state machine to control device operation. A flowchart is shown in Figure 4. On initial power-up, if  $V_{IN}$  < UVLO or if  $V_{IN}$  > OVLO, GATE is held at 0V, and FLAG is high.

If UVLO <  $V_{IN}$  < OVLO, the device enters startup after a 50ms internal delay. The internal charge pump is enabled, and GATE begins to be driven above  $V_{IN}$  by the internal charge pump. FLAG is held high during startup until the FLAG blanking period expires, typically 50ms after the GATE starts going high. At this point the device is in its on state.

At any time if  $V_{\text{IN}}$  drops below UVLO or  $V_{\text{IN}}$  is greater than OVLO, FLAG is driven high and GATE is driven to ground.

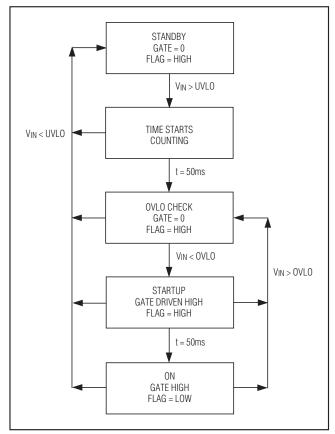


Figure 4. State Diagram

### **Applications Information**

#### **MOSFET Configuration**

The MAX4843–MAX4846 can be used with either a single MOSFET configuration as shown in the *Typical Operating Circuit*, or can be configured with a back-to-back MOSFET as shown in Figure 5. The back-to-back configuration has almost zero reverse current when the input supply is below the output.

If reverse current leakage is not a concern, a single MOSFET can be used. This approach has half the loss of the back-to-back configuration when used with similar MOSFET types and is a lower cost solution. Note that if the input is actually pulled low, the output is also pulled low due to the parasitic body diode in the MOSFET. If this is a concern, the back-to-back configuration should be used.

In a typical application of the MAX4846, an external adapter with built-in battery charger is connected to IN and a battery is connected to the source of the external FET. When the adapter is unplugged, IN is directly connected to the battery through the external FET. Since the battery voltage is typically greater than 3V, the GATE voltage stays high and the device remains powered by the battery.

#### **MOSFET Selection**

The MAX4843–MAX4846 are designed for use with either a single n-channel MOSFET or dual back-to-back n-channel MOSFETs. In most situations, MOSFETs with RON specified for a VGS of 4.5V work well. If the input supply is near the UVLO maximum of 3.5V, consider using a MOSFET specified for a lower VGS voltage. Also the VDS should be 30V for the MOSFET to withstand the full 28V IN range of the MAX4843–MAX4846. Table 1 shows a selection of MOSFETs appropriate for use with the MAX4843–MAX4846.

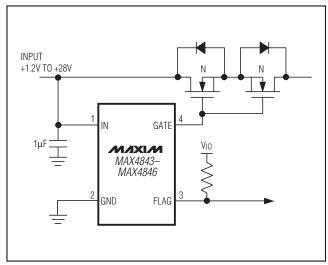


Figure 5. Back-to-Back External MOSFET Configuration

#### **IN Bypass Considerations**

For most applications, bypass IN to GND with a  $1\mu F$  ceramic capacitor. If the power source has significant inductance due to long lead length, take care to prevent overshoots due to the LC tank circuit and provide protection if necessary to prevent exceeding the 30V absolute maximum rating on IN.

The MAX4843–MAX4846 provide protection against voltage faults up to 28V, but this does not include negative voltages. If negative voltages are a concern, connect a Schottky diode from IN to GND to clamp negative input voltages.

#### **ESD Test Conditions**

ESD performance depends on a number of conditions. The MAX4843-MAX4846 are protected from ±15kV typical ESD on IN when IN is bypassed to ground with a 1µF ceramic capacitor.

**Table 1. MOSFET Suggestions** 

PART	CONFIGURATION/ PACKAGE	V <sub>DS</sub> MAX (V)	R <sub>ON</sub> at 4.5V (mΩ)	MANUFACTURER
Si5902DC	Dual/1206-8	30	143	Vishay Siliconix
Si1426DH	Single/SSOT-6	30	115	www.vishay.com
FDC6561AN	Dual/SSOT-6	30	145	Fairchild Semiconductor
FDC6305N	Dual/SSOT-6	20	80	www.fairchildsemi.com

#### **Human Body Model**

Figure 6 shows the Human Body Model and Figure 7 shows the current waveform it generates when discharged into a low impedance. This model consists of a 100pF capacitor charged to the ESD voltage of interest, which is then discharged into the device through a  $1.5k\Omega$  resistor.

#### IEC 1000-4-2

Since January 1996, all equipment manufactured and/or sold in the European Union has been required to meet the stringent IEC 1000-4-2 specification. The IEC 1000-4-2 standard covers ESD testing and performance of finished equipment; it does not specifically refer to integrated circuits. The MAX4843–MAX4846

help users design equipment that meets Level 3 of IEC 1000-4-2, without additional ESD-protection components.

The main difference between tests done using the Human Body Model and IEC 1000-4-2 is higher peak current in IEC 1000-4-2. Because series resistance is lower in the IEC 1000-4-2 ESD test model (Figure 8), the ESD withstand voltage measured to this standard is generally lower than that measured using the Human Body Model. Figure 9 shows the current waveform for the ±8kV IEC 1000-4-2 Level 4 ESD Contact Discharge test. The Air-Gap test involves approaching the device with a charger probe. The Contact Discharge method connects the probe to the device before the probe is energized.

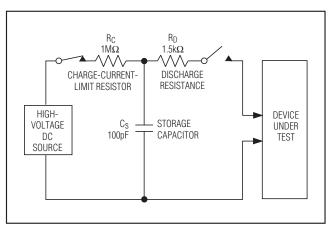


Figure 6. Human Body ESD Test Model

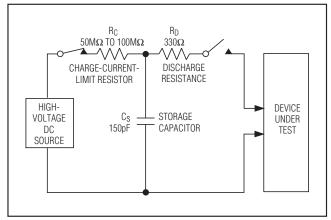


Figure 8. IEC 1000-4-2 ESD Test Model

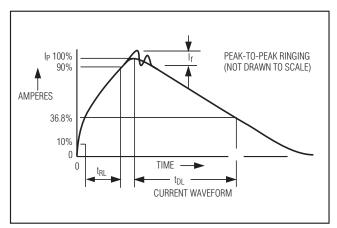


Figure 7. Human Body Model Current Waveform

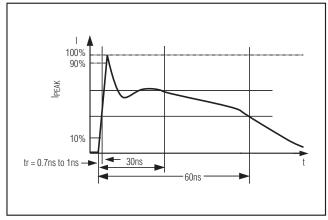


Figure 9. IEC 1000-4-2 ESD Generator Current Waveform

# Overvoltage Protection Switches with Low Standby Current

\_\_Chip Information

**Package Information** 

For the latest package outline information and land patterns, go to **www.maxim-ic.com/packages**.

PACKAGE TYPE	PACKAGE CODE	DOCUMENT NO.
6 µDFN	L611-1	<u>21-0147</u>
6 UTLGA	Y61A1-1	21-0190

PROCESS: BICMOS

# Overvoltage Protection Switches with Low Standby Current

### **Revision History**

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	4/05	Initial release	_
3	2/08	Added packaging, removed SC70	1, 2, 4, 7, 9
4	8/09	Added MAX4845A and MAX4845C to Ordering Information and Electrical Characteristics.	1, 2
5	12/09	Removed MAX4845A and added MAX4845D to Ordering Information and Electrical Characteristics.  Updated Undervoltage Lockout (UVLO) section under Detailed Description to include MAX4845D.	1, 2, 6

Maxim cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim product. No circuit patent licenses are implied. Maxim reserves the right to change the circuitry and specifications without notice at any time.